

NTP75N03L09, NTB75N03L09

Power MOSFET 75 Amps, 30 Volts N-Channel TO-220 and D²PAK

This Logic Level Vertical Power MOSFET is a general purpose part that provides the “best of design” available today in a low cost power package. Avalanche energy issues make this part an ideal design in. The drain-to-source diode has a ideal fast but soft recovery.

Features

- Ultra-Low $R_{DS(on)}$, Single Base, Advanced Technology
- SPICE Parameters Available
- Diode is Characterized for Use in Bridge Circuits
- I_{DSS} and $V_{DS(on)}$ Specified at Elevated Temperatures
- High Avalanche Energy Specified
- ESD JEDAC Rated HBM Class 1, MM Class B, CDM Class 0

Typical Applications

- Power Supplies
- Inductive Loads
- PWM Motor Controls
- Replaces MTP75N03HDL and MTB75N03HDL in Many Applications



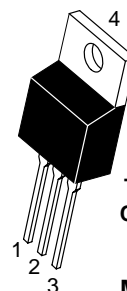
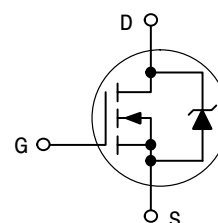
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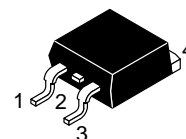
**75 AMPERES
30 VOLTS**

$R_{DS(on)} = 8\text{ m}\Omega$

N-Channel

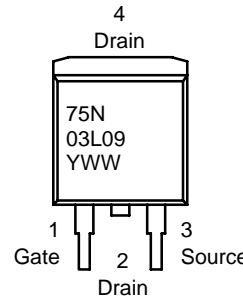
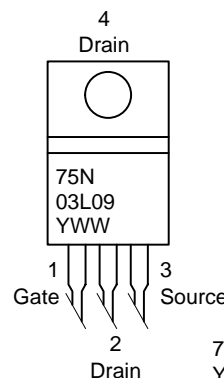


**TO-220AB
CASE 221A
STYLE 5**



**D2PAK
CASE 418B
STYLE 2**

MARKING DIAGRAMS & PIN ASSIGNMENTS



75N03L09 = Device Code
Y = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
NTP75N03L09	TO-220	50 Units/Rail
NTB75N03L09	D2PAK	50 Units/Rail
NTB75N03L09T4	D2PAK	800/Tape & Reel

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MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	30	Vdc
Drain-to-Gate Voltage (R _{GS} = 10 MΩ)	V _{DGB}	30	Vdc
Gate-to-Source Voltage - Continuous	V _{GS}	±20	Vdc
Non-repetitive (tp ≤ 10 ms)	V _{GS}	±24	Vdc
Drain Current - Continuous @ T _A = 25°C - Continuous @ T _A = 100°C - Single Pulse (tp ≤ 10 μs)	I _D I _D I _{DM}	75 59 225	Adc Adc Apk
Total Power Dissipation @ T _C = 25°C Derate above 25°C Total Power Dissipation @ T _A = 25°C (Note 1)	P _D	150 1.0 2.5	W W/°C W
Operating and Storage Temperature Range	T _J and T _{stg}	-55 to 150	°C
Single Pulse Drain-to-Source Avalanche Energy - Starting T _J = 25°C (V _{DD} = 38 Vdc, V _{GS} = 10 Vdc, L = 1 mH, I _{L(pk)} = 55 A, V _{DS} = 40 Vdc)	E _{AS}	1500	mJ
Thermal Resistance - Junction-to-Case - Junction-to-Ambient - Junction-to-Ambient (Note 1)	R _{θJC} R _{θJA} R _{θJA}	1.0 62.5 50	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T _L	260	°C

1. When surface mounted to an FR4 board using the minimum recommended pad size.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ.	Max	Unit
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OFF CHARACTERISTICS

Drain - Source Breakdown Voltage (Note 2) (V _{GS} = 0 Vdc, I _D = 250 μAdc) Temperature Coefficient (Negative)	V _{(BR)DSS}	30	34 -57	- -	Vdc mV°C
Zero Gate Voltage Drain Current (V _{DS} = 30 Vdc, V _{GS} = 0 Vdc) (V _{DS} = 30 Vdc, V _{GS} = 0 Vdc, T _J = 150°C)	I _{DSS}	- -	- -	1.0 10	μAdc
Gate-Body Leakage Current (V _{GS} = ±20 Vdc, V _{DS} = 0 Vdc)	I _{GSS}	-	-	±100	nAdc

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage (Note 2) (V _{DS} = V _{GS} , I _D = 250 μAdc) Threshold Temperature Coefficient (Negative)	V _{GS(th)}	1.0 -	1.6 -6	2.0 -	Vdc mV°C
Static Drain-to-Source On-Resistance (Note 2) (V _{GS} = 5.0 Vdc, I _D = 37.5 Adc)	R _{DS(on)}	-	6.5	8.0	mΩ
Static Drain-to-Source On Resistance (Note 2) (V _{GS} = 10 Vdc, I _D = 75 Adc) (V _{GS} = 10 Vdc, I _D = 37.5 Adc, T _J = 125°C)	V _{DS(on)}	- -	0.52 0.35	0.68 0.50	Vdc
Forward Transconductance (Notes 2 & 4) (V _{DS} = 3 Vdc, I _D = 20 Adc)	g _{FS}	-	58	-	mΩ

DYNAMIC CHARACTERISTICS (Note 4)

Input Capacitance	(V _{DS} = 25 Vdc, V _{GS} = 0, f = 1.0 MHz)	C _{iss}	-	4398	5635	pF
Output Capacitance		C _{oss}	-	1160	1894	
Transfer Capacitance		C _{rss}	-	317	430	

SWITCHING CHARACTERISTICS (Notes 3 & 4)

Turn-On Delay Time	(V _{GS} = 5.0 Vdc, V _{DD} = 20 Vdc, I _D = 75 Adc, R _G = 4.7 Ω) (Note 2)	t _{d(on)}	-	16	30	ns
Rise Time		t _r	-	130	200	
Turn-Off Delay Time		t _{d(off)}	-	65	110	
Fall Time		t _f	-	105	175	
Gate Charge	(V _{GS} = 5.0 Vdc, I _D = 75 Adc, V _{DS} = 24 Vdc) (Note 2)	Q _T	-	52	122	nC
		Q ₁	-	6.6	28	
		Q ₂	-	28	66	

SOURCE-DRAIN DIODE CHARACTERISTICS

Forward On-Voltage	(I _S = 75 Adc, V _{GS} = 0 Vdc) (I _S = 75 Adc, V _{GS} = 0 Vdc, T _J = 125°C) (Note 2)	V _{SD}	- -	1.19 1.09	1.25 -	Vdc
Reverse Recovery Time (Note 4)	(I _S = 75 Adc, V _{GS} = 0 Vdc di/dt = 100 A/μs) (Note 2)	t _{rr}	-	37	-	ns
		t _a	-	20	-	
Reverse Recovery Stored Charge (Note 4)		t _b	-	17	-	μC
		Q _{RR}	-	0.023	-	

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
3. Switching characteristics are independent of operating junction temperatures.
4. From characterization test data.

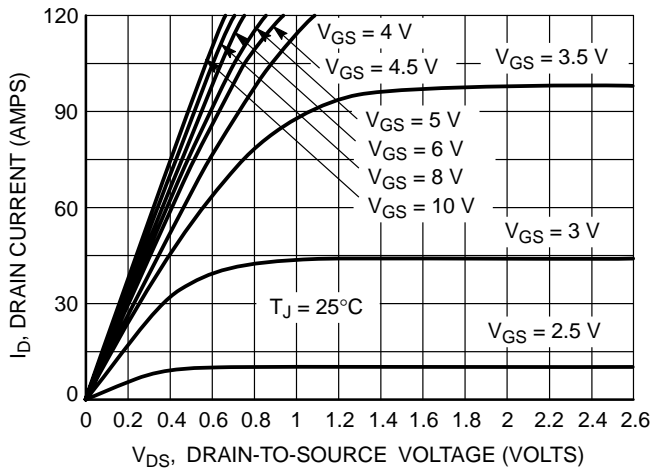


Figure 1. On-Region Characteristics

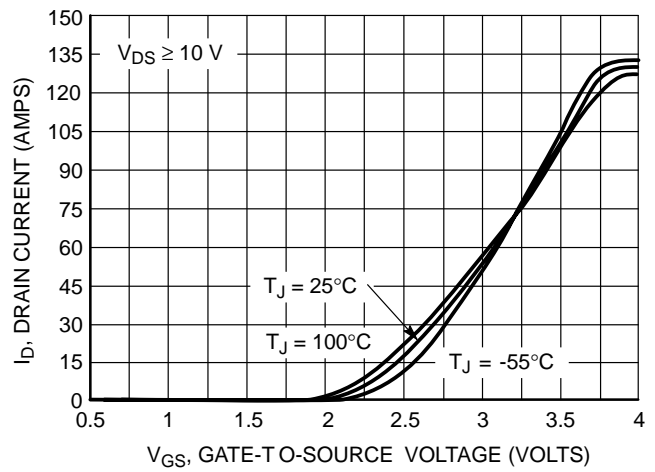


Figure 2. Transfer Characteristics

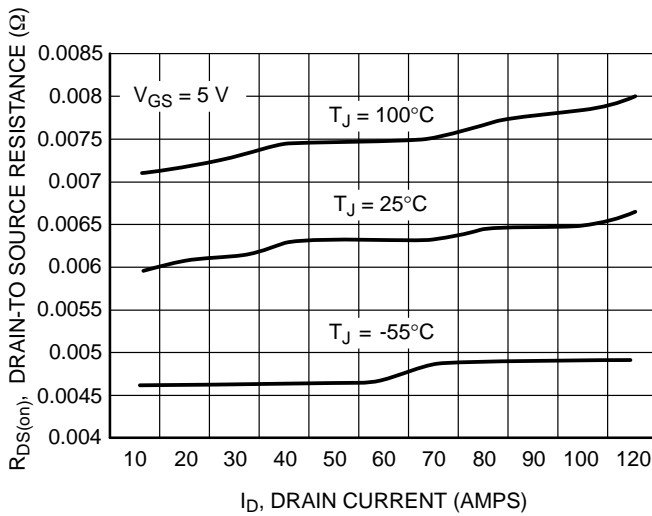


Figure 3. On-Resistance vs. Drain Current and Temperature

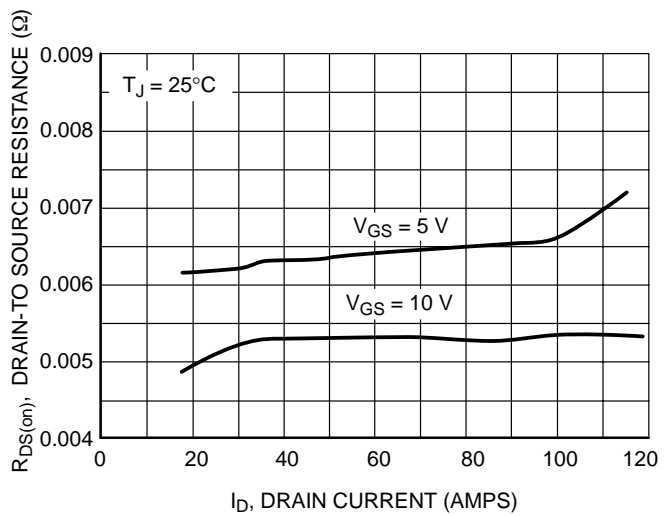


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

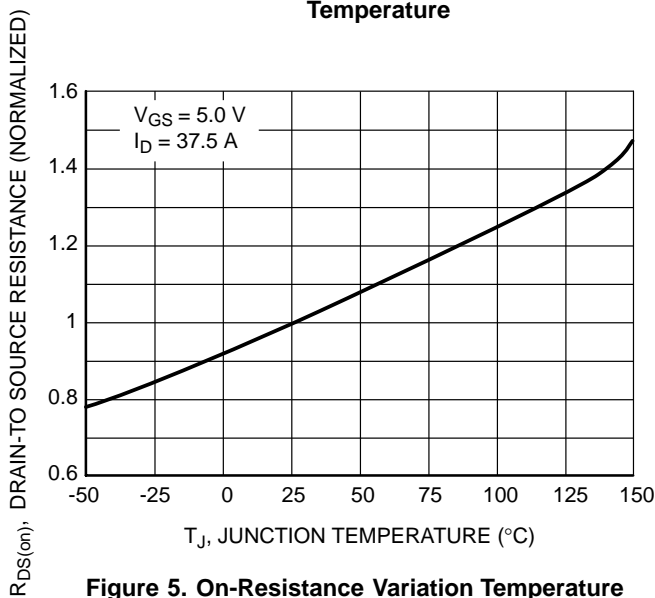


Figure 5. On-Resistance Variation Temperature

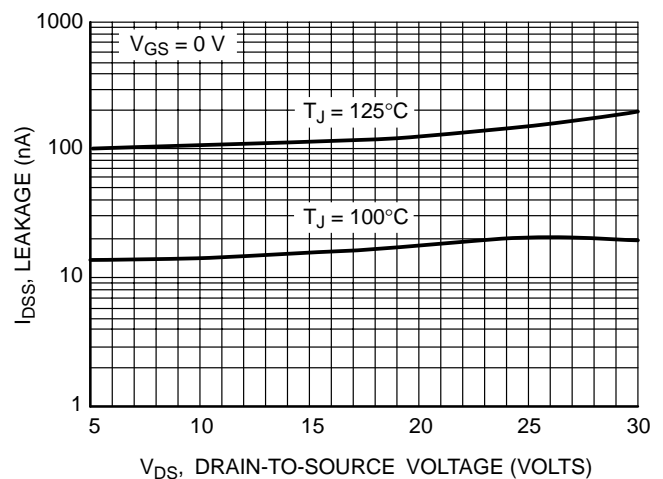


Figure 6. Drain-to-Source Leakage Current vs. Voltage

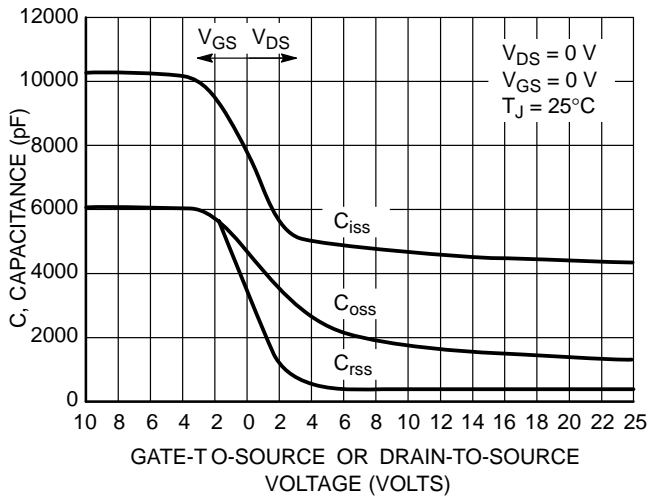


Figure 7. Capacitance Variation

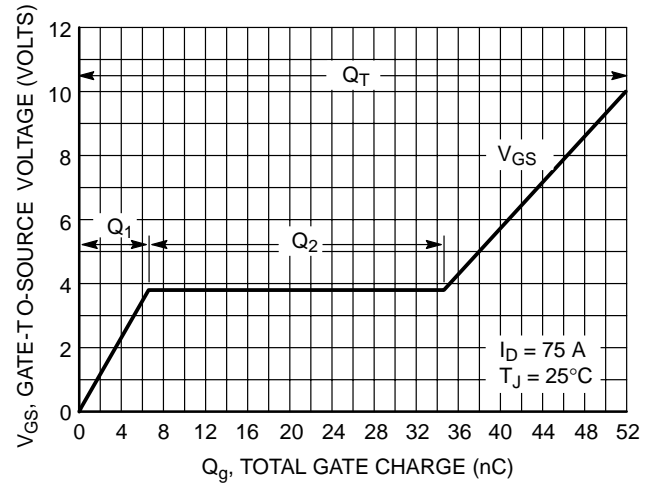


Figure 8. Gate-to-Source Voltage vs. Total Charge

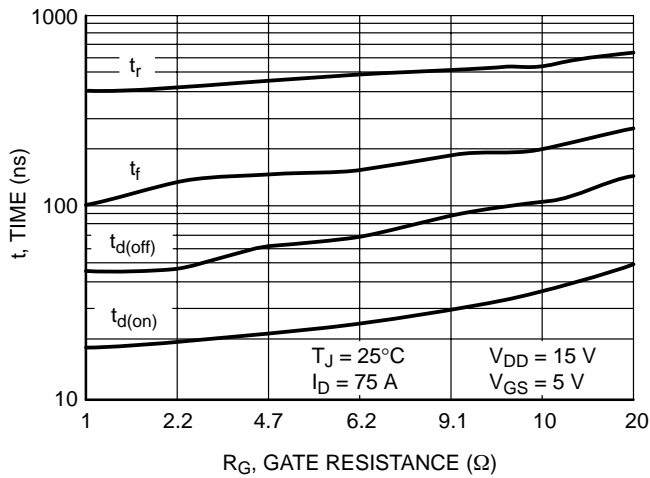


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

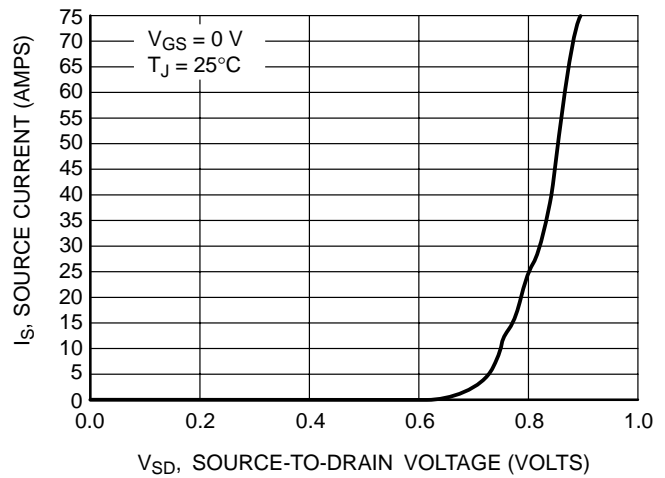


Figure 10. Diode Forward Voltage vs. Current

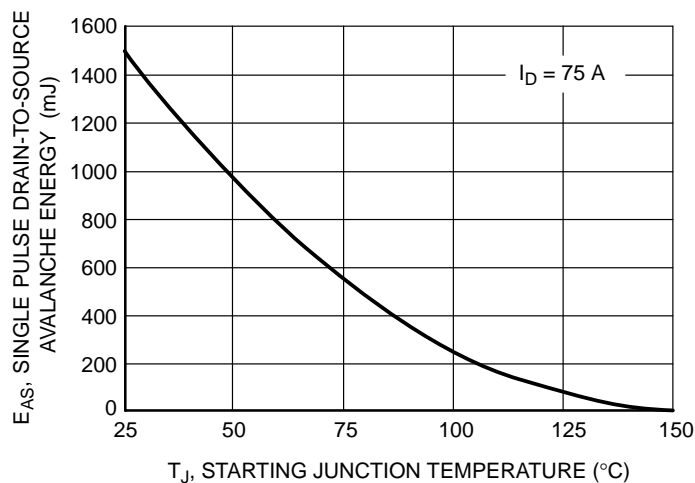
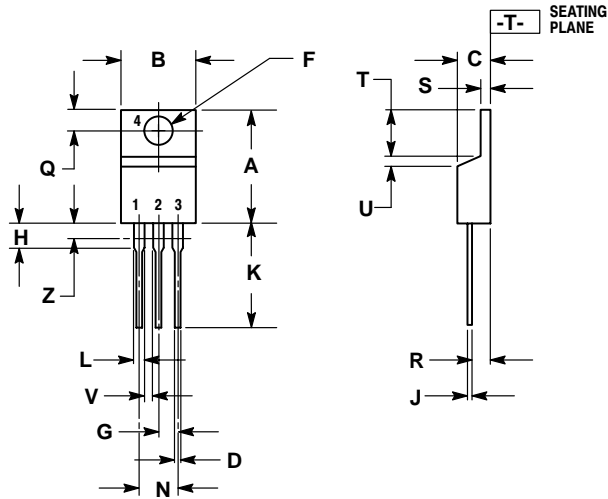


Figure 11. Maximum Avalanche Energy vs. Starting Junction Temperature

NTP75N03L09, NTB75N03L09

PACKAGE DIMENSIONS

TO-220 THREE-LEAD
TO-220AB
CASE 221A-09
ISSUE AA



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

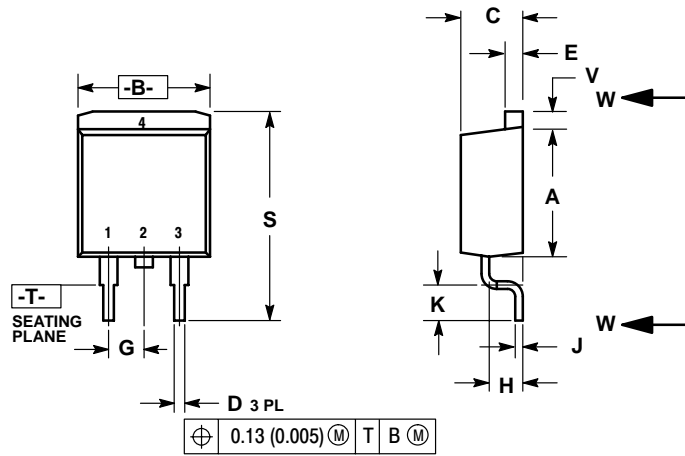
STYLE 5:

- PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

NTP75N03L09, NTB75N03L09

PACKAGE DIMENSIONS

D²PAK
CASE 418B-04
ISSUE H




NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100	BSC	2.54	BSC
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197	REF	5.00	REF
P	0.079	REF	2.00	REF
R	0.039	REF	0.99	REF
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

STYLE 2:

- PIN 1. GATE
- DRAIN
- SOURCE
- DRAIN

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